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The invention relates to the technology of oxide semiconductors, in particular to gas sensors based on molybdenum oxide.

The gas sensor based on MoO_3 comprises a dielectric substrate, on one side of which is placed a sensitive layer of MoO_3 , with ohmic contacts applied on it, forming the sensitive zone, and on the opposite surface of the substrate is applied a heating element. The sensitive layer is made in the form of a nanocrystalline strip of a thickness of 150 nm and a width of the sensitive zone of 150 μm .

Claims: 1

Fig.: 4